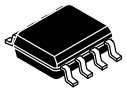
CM1216

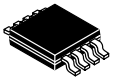
6 and 8-Channel Low Capacitance ESD Arrays

ON Semiconductor®

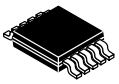
http://onsemi.com



SOIC−8
SM SUFFIX
CASE 751AC



MSOP−8
MR SUFFIX
CASE 846AD



MSOP−10
MR SUFFIX
CASE 846AE

Product Description

The CM1216 family of diode arrays provide sESD protection for electronic components or sub−systems requiring minimal capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes in series which steer the positive or negative ESD current pulse to either the positive (V_P) or negative (V_N) supply rail. The CM1216 protects against ESD pulses up to ±15 kV per the IEC 61000−4−2 standard.

This device is particularly well−suited for protecting systems using high−speed ports such as USB2.0, IEEE1394 (Firewire®, iLink™), Serial ATA, DVI, HDMI and corresponding ports in removable storage, digital camcorders, DVD−RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

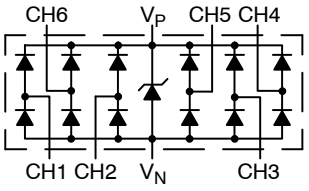
Features

- Six and Eight Channels of ESD Protection
- Provides ±15 kV ESD Protection on Each Channel per the IEC 61000−4−2 ESD Requirements
- Channel Loading Capacitance of 1.6 pF Typical
- Channel I/O to GND Capacitance Difference of 0.04 pF Typical
- Mutual Capacitance of 0.13 pF Typical
- Minimal Capacitance Change with Temperature and Voltage
- Each I/O Pin Can Withstand Over 1000 ESD Strikes
- SOIC and MSOP Packages
- These Devices are Pb−Free and are RoHS Compliant

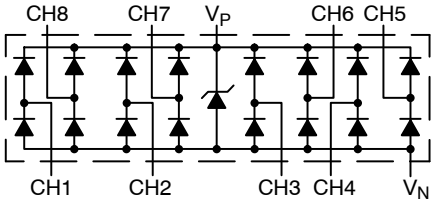
Applications

- IEEE1394 Firewire® Ports at 400 Mbps / 800 Mbps
- DVI Ports, HDMI Ports in Notebooks, Set Top Boxes, Digital TVs, LCD Displays
- Serial ATA Ports in Desktop PCs and Hard Disk Drives
- PCI Express Ports
- General Purpose High−Speed Data Line ESD Protection

BLOCK DIAGRAM

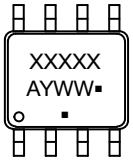


CM1216−06SM
CM1216−06MR



CM1216−08MR

MARKING DIAGRAM



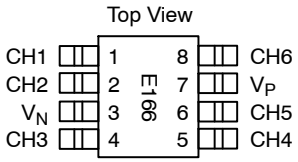
XXXXXX	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week
▪	= Pb−Free Package

ORDERING INFORMATION

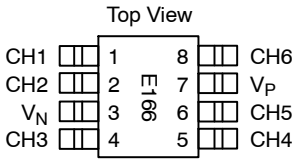
Device	Package	Shipping†
CM1216−06SM	SOIC (Pb−Free)	2500/Tape & Reel
CM1216−06MR	MSOP (Pb−Free)	4000/Tape & Reel
CM1216−08MR	MSOP (Pb−Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

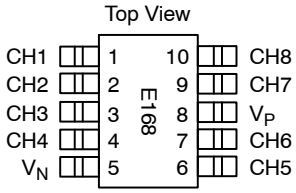
PACKAGE / PINOUT DIAGRAMS



8−Pin SOIC−8



8−Pin MSOP−8



10−Pin MSOP−10

Table 1. PIN DESCRIPTIONS

Pin Name	MSOP−8	SOIC−8	MSOP−10	Type	Description
	Pin No.	Pin No.	Pin No.		
CH1	1	1	1	I/O	ESD Channel
CH2	2	2	2	I/O	ESD Channel
CH3	4	4	3	I/O	ESD Channel
CH4	5	5	4	I/O	ESD Channel
V_N	3	3	5	GND	Negative voltage supply rail
CH5	6	6	6	I/O	ESD Channel
CH6	8	8	7	I/O	ESD Channel
V_P	7	7	8	PWR	Positive voltage supply rail
CH7	–	–	9	I/O	ESD Channel
CH8	–	–	10	I/O	ESD Channel

SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Operating Supply Voltage (V_P−V_N)	6	V
Diode Forward DC Current	20	μA
DC Voltage at any Channel Input	(V_N−0.5) to (V_P+0.5)	V
Operating Temperature Range Ambient Junction	 −40 to +85 −40 to +125	°C
Storage Temperature Range	−40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. STANDARD OPERATING CONDITIONS

Parameter	Rating	Units
Temperature Range (Ambient)	−40 to +85	°C
Package Power Rating MSOP8 Package (CM1216−06MR) SOIC8 Package (CM1216−06SM) MSOP10 Package (CM1216−08MR)	 400 600 400	mW

Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_P	Operating Supply Voltage (V_P–V_N)			3.3	5.5	V
I_P	Operating Supply Current	(V_P–V_N) = 3.3 V			8	μA
V_F	Diode Forward Voltage Top Diode Bottom Diode	I_F = 20 μA; T_A = 25°C	 0.6 0.6	 0.8 0.8	 0.95 0.95	V
I_{LEAK}	Channel Leakage Current	T_A = 25°C; V_P = 5 V, V_N = 0 V		±0.1	±1.0	μA
C_{IN}	Channel Input Capacitance	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V (Note 2)		1.6	2.0	pF
ΔC_{IN}	Channel Input Capacitance Matching			0.04		pF
C_{MUTUAL}	Mutual Capacitance	(V_P–V_N) = 3.3 V		0.13		pF
V_{ESD}	ESD Protection Peak Discharge Voltage at any channel input, in system, contact discharge per IEC 61000–4–2 standard	T_A = 25°C (Notes 2 and 3)	 ±15			kV
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	I_{PP} = 1 A, t_P = 8/20 μS; T_A = 25°C		 +9.0 –1.5		V
R_{DYN}	Dynamic Resistance Positive transients Negative transients	I_{PP} = 1 A, t_P = 8/20 μS; T_A = 25°C		 0.6 0.4		Ω

1. All parameters specified at T_A = –40°C to +85°C unless otherwise noted.
2. Standard IEC 61000–4–2 with $C_{Discharge}$ = 150 pF, $R_{Discharge}$ = 330 Ω, V_P = 3.3 V, V_N grounded.
3. From I/O pins to V_P or V_N only. V_P bypassed to V_N with low ESR 0.2 μF ceramic capacitor.

PERFORMANCE CHARACTERISTICS

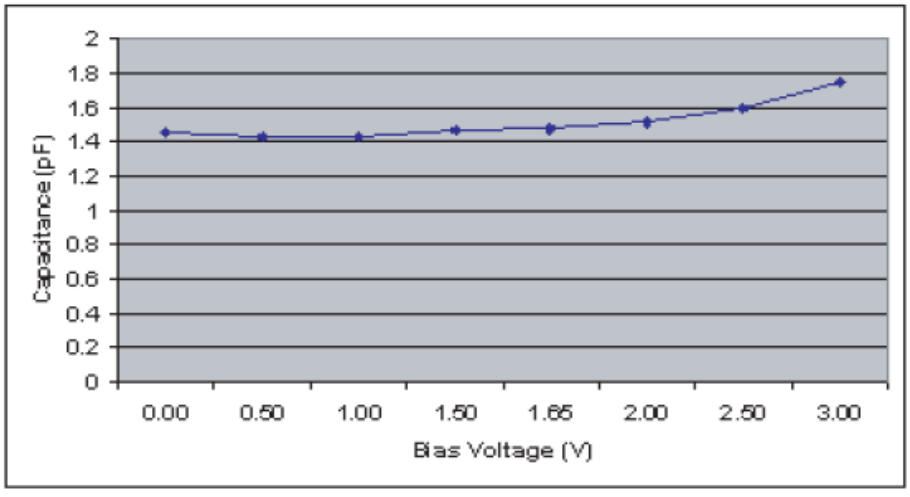


Figure 1. Typical Variation of C_{IN} vs. V_{IN}
(f = 1 MHz, V_P= 3.3 V, V_N = 0 V, 0.1 μF Chip Capacitor between V_P and V_N, T_A = 25°C)

APPLICATION INFORMATION

Design Considerations

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Application of Positive ESD Pulse between Input Channel and Ground, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by L_1 and L_2. The voltage V_{CL} on the line being protected is:

$$\mathbf{V_{CL} = Fwd\ voltage\ drop\ of\ D_1 + V_{SUPPLY} + L_1 \times d(I_{ESD}) / dt + L_2 \times d(I_{ESD}) / dt}$$

where I_{ESD} is the ESD current pulse, and V_{SUPPLY} is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000−4−2 standard results in a current pulse that rises from zero to 30 Amps in 1 ns. Here $d(I_{ESD})/dt$ can be approximated by $\Delta I_{ESD}/\Delta t$, or $30/(1x10^{-9})$. So just 10 nH of series inductance (L_1 and L_2 combined) will lead to a 300 V increment in V_{CL}!

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

The CM1213 has an integrated Zener diode between V_P and V_N. This greatly reduces the effect of supply rail inductance L_2 on V_{CL} by clamping V_P at the breakdown voltage of the Zener diode. However, for the lowest possible V_{CL}, especially when V_P is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a 0.22 μF ceramic chip capacitor be connected between V_P and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the V_P pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

Additional Information

See also ON Semiconductor Application Note, “Design Considerations for ESD Protection”, in the Applications section.

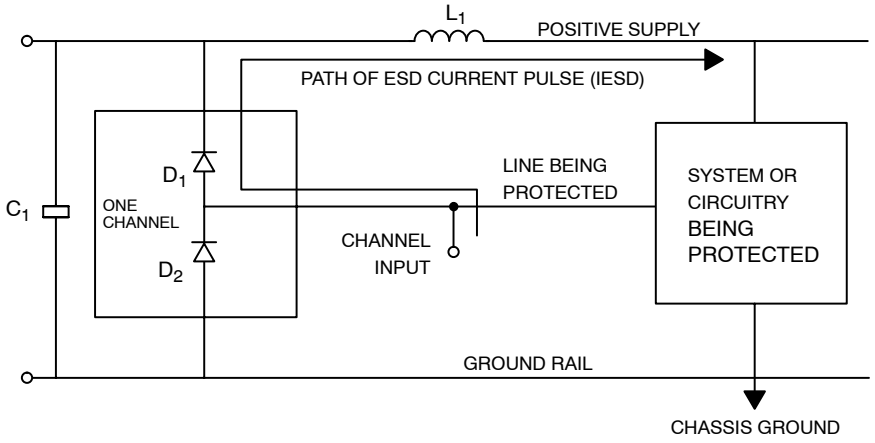
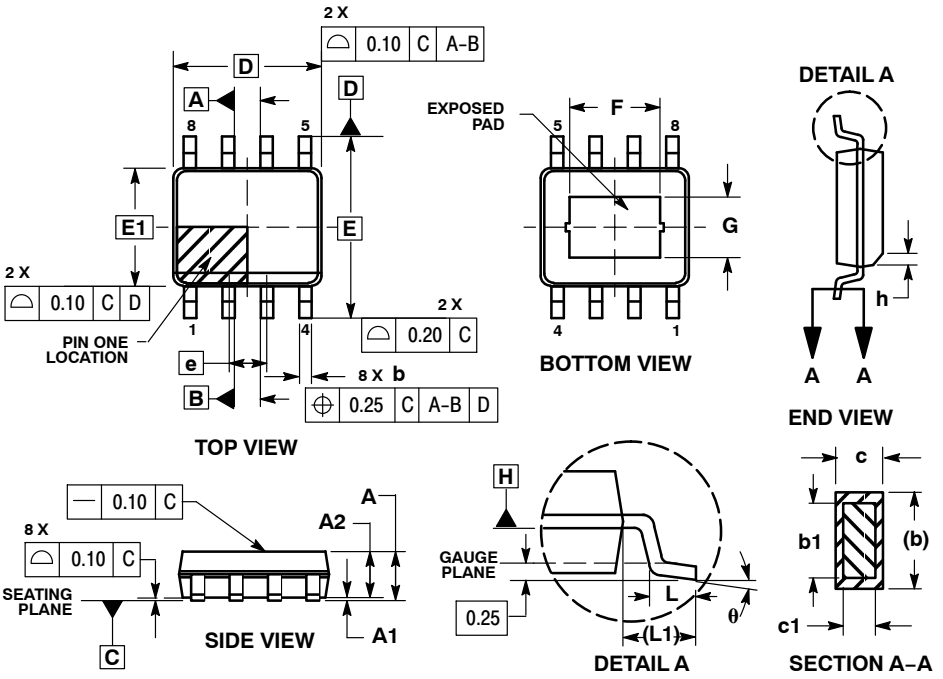


Figure 2. Application of Positive ESD Pulse between Input Channel and Ground

PACKAGE DIMENSIONS

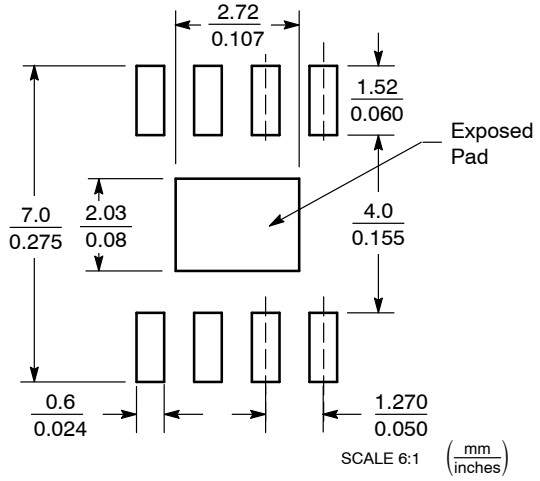
SOIC−8 EP
CASE 751AC−01
ISSUE B



NOTES:
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. DIMENSIONS IN MILLIMETERS (ANGLES IN DEGREES).
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM TOTAL IN EXCESS OF THE “b” DIMENSION AT MAXIMUM MATERIAL CONDITION.
4. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.

	MILLIMETERS	
DIM	MIN	MAX
A	1.35	1.75
A1	0.00	0.10
A2	1.35	1.65
b	0.31	0.51
b1	0.28	0.48
c	0.17	0.25
c1	0.17	0.23
D	4.90 BSC	
E	6.00 BSC	
E1	3.90 BSC	
e	1.27 BSC	
L	0.40	1.27
L1	1.04 REF	
F	2.24	3.20
G	1.55	2.51
h	0.25	0.50
θ	0 °	8 °

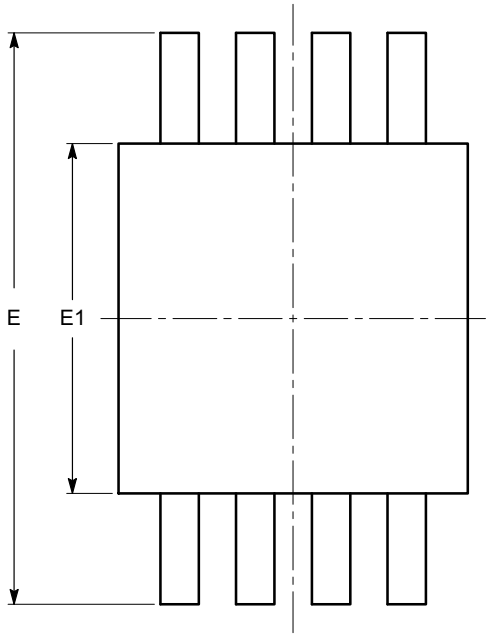
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

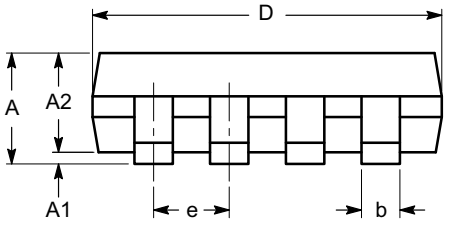
PACKAGE DIMENSIONS

MSOP 8, 3x3
CASE 846AD−01
ISSUE O

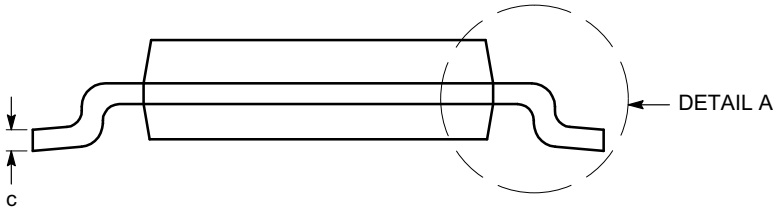


TOP VIEW

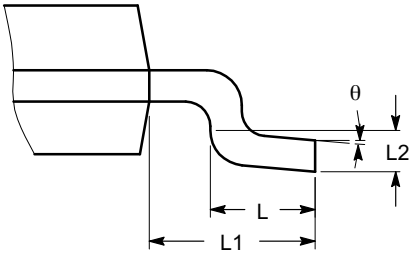
SYMBOL	MIN	NOM	MAX
A			1.10
A1	0.05	0.10	0.15
A2	0.75	0.85	0.95
b	0.22		0.38
c	0.13		0.23
D	2.90	3.00	3.10
E	4.80	4.90	5.00
E1	2.90	3.00	3.10
e	0.65 BSC		
L	0.40	0.60	0.80
L1	0.95 REF		
L2	0.25 BSC		
θ	0°		6°



SIDE VIEW



END VIEW

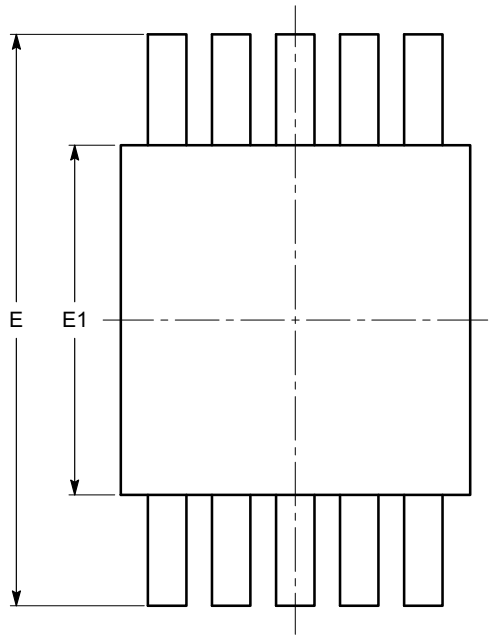


DETAIL A

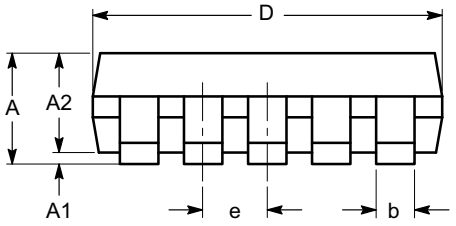
Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-187.

PACKAGE DIMENSIONS

MSOP 10, 3x3
CASE 846AE−01
ISSUE O

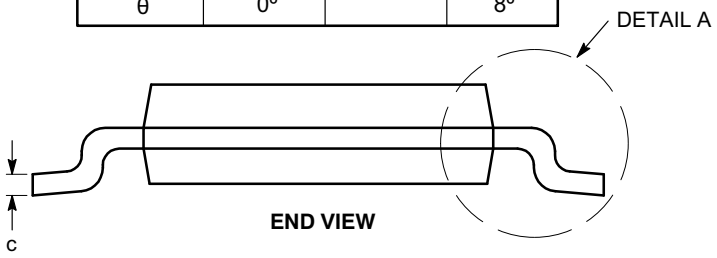


TOP VIEW

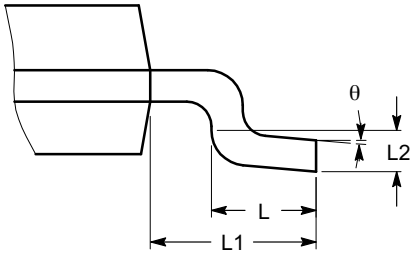


SIDE VIEW

SYMBOL	MIN	NOM	MAX
A			1.10
A1	0.00	0.05	0.15
A2	0.75	0.85	0.95
b	0.17		0.27
c	0.13		0.23
D	2.90	3.00	3.10
E	4.75	4.90	5.05
E1	2.90	3.00	3.10
e		0.50 BSC	
L	0.40	0.60	0.80
L1		0.95 REF	
L2		0.25 BSC	
θ	0°		8°



END VIEW



DETAIL A

Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-187.

FireWire is a registered trademark of Apple Computer. Inc.
iLink is a trademark of S. J. Electro Systems, Inc.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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